Silicon PNP Epitaxial

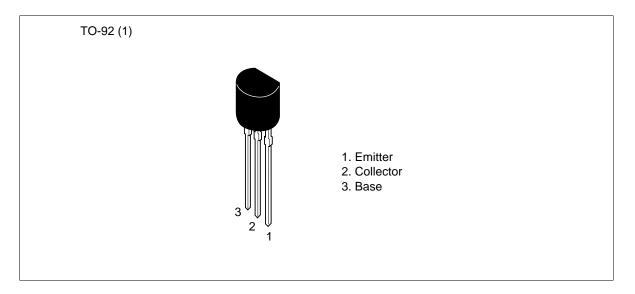
HITACHI

ADE-208-1001 (Z) 1st. Edition Mar. 2001

Application

- Low frequency low noise amplifier
- Complementary pair with 2SC1775/A

Outline





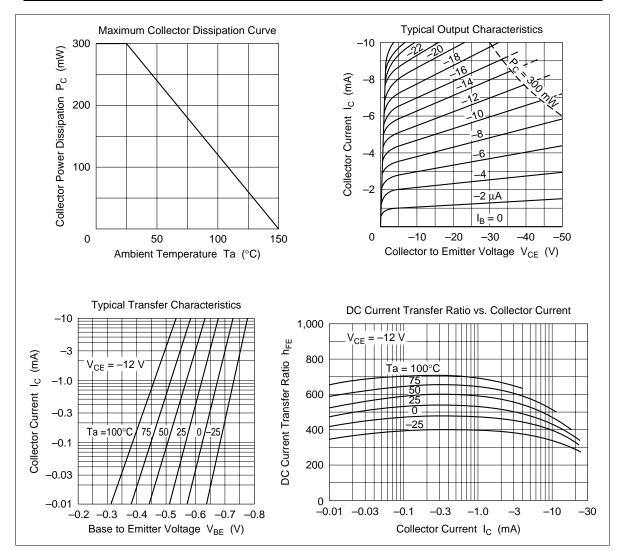
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

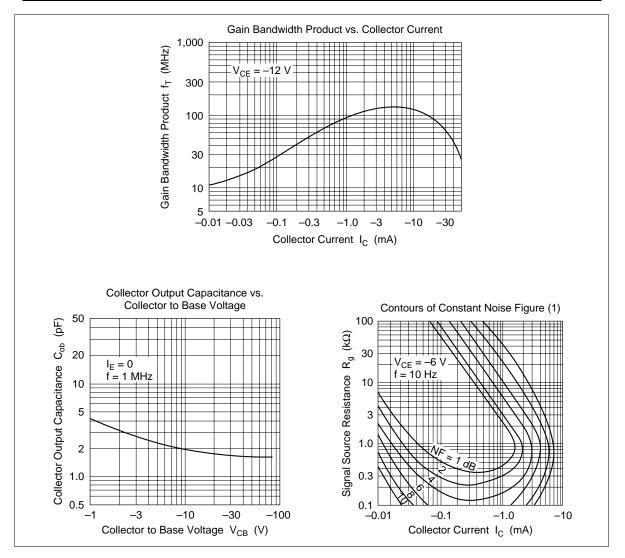
Item	Symbol	2SA872	2SA872A	Unit
Collector to base voltage	V _{CBO}	-90	-120	V
Collector to emitter voltage	V _{CEO}	-90	-120	V
Emitter to base voltage	V _{EBO}	-5	-5	V
Collector current	Ι _c	-50	-50	mA
Collector power dissipation	Pc	300	300	mW
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-50 to +150	°C

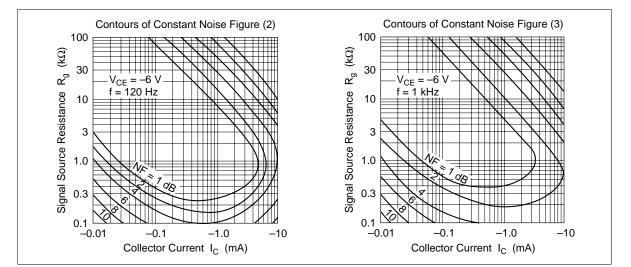
Electrical Characteristics (Ta = 25°C)

		2SA8	72		2SA872A				
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	-90		_	-120		_	V	$I_c = -1 \text{ mA}, \text{ R}_{\text{BE}} = \infty$
Collector cutoff current	I _{CBO}	_	_	-0.5	_	_	_	μΑ	$V_{\rm CB} = -75 \ V, \ I_{\rm E} = 0$
		—	—	—	—	—	-0.5	μΑ	$V_{ce} = -100 \text{ V}, I_{e} = 0$
DC current tarnsfer ratio	h_{FE1}^{*1}	250	—	800	250	—	800		$V_{ce} = -12 V,$ $I_c = -2 mA$
	h _{FE2}	160	_	_	160	_	_		$V_{ce} = -12 V,$ $I_c = -0.1 mA$
Base to emitter voltage	V_{BE}	_	_	-0.75	—	_	-0.75	V	$V_{ce} = -12 V,$ $I_c = -2 mA$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_		-0.5			-0.5	V	$I_{c} = -10 \text{ mA},$ $I_{B} = -1 \text{ mA}$
Gain bandwidth product	f _T	_	120	_	—	120	_	MHz	$V_{ce} = -12 V,$ $I_{c} = -2 mA$
Collector output capacitance	Cob	_	1.8	_	—	1.8	_	pF	$V_{CB} = -25 \text{ V}, \text{ I}_{E} = 0,$ f = 1 MHz
Noise figure	NF	_	—	5.0	—	_	5.0	dB	$ \begin{array}{c} V_{\rm CE} = -6 \ V, \ f = 10 \ Hz \\ I_{\rm C} = -50 \ \mu A \\ R_{\rm g} = 50 \ k\Omega \end{array} $
		_	_	1.5		_	1.5	dB	f = 1 kHz

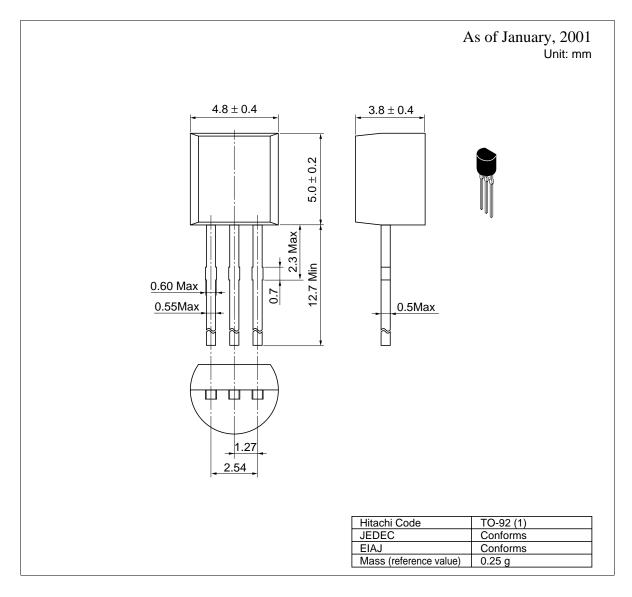
250 to 500 400 to 800







Package Dimensions



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Hitachi, Ltd.

Semiconductor & Integrated Circuits. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica Europe	: http://semiconductor.hitachi.com/ : http://www.hitachi-eu.com/hel/ecg
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose,CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH Electronic Components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel : <886>-(2)-2718-3666 Tel: <44> (1628) 585000 Fax: <44> (1628) 585160

Hitachi Asia Ltd. Hitachi Tower 16 Collyer Quay #20-00, Singapore 049318 Tel : <65>-538-6533/538-8577 Fax : <65>-538-6933/538-3877 URL : http://www.hitachi.com.sg

Hitachi Asia Ltd (Taipei Branch Office) 4/F, No. 167, Tun Hwa North Road, Hung-Kuo Building. Taipei (105), Taiwan Fax : <886>-(2)-2718-8180 Telex : 23222 HAS-TP URL : http://www.hitachi.com.tw

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852>-(2)-735-9218 Fax : <852>-(2)-730-0281 URL : http://www.hitachi.com.hk

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